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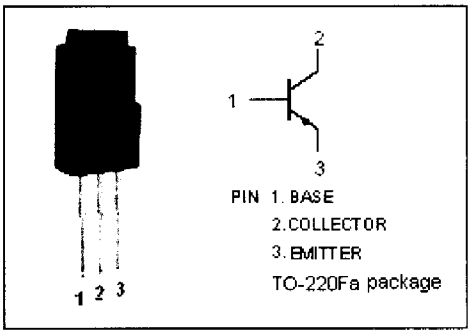
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Silicon PNP Power Transistor

2SA1304

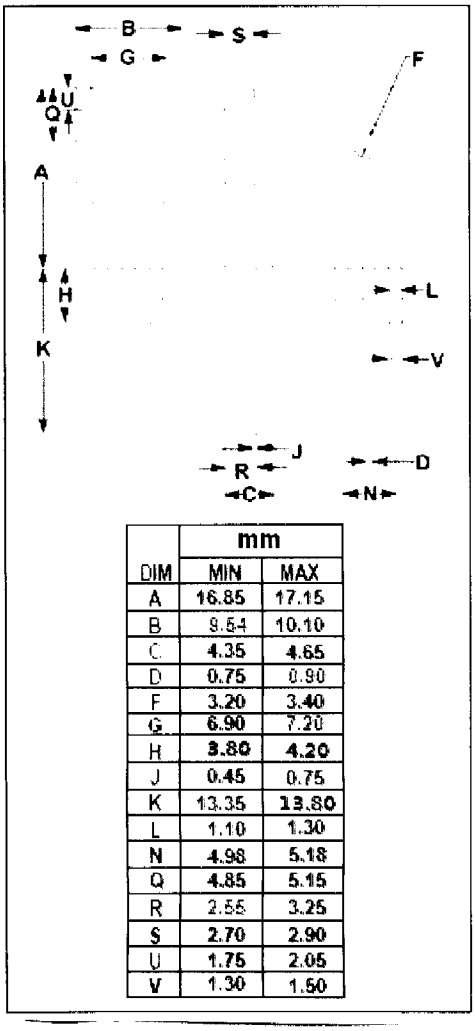


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -150V(Min)
- Complement to Type 2SC3296

APPLICATIONS

- Power amplifier applications.
- Vertical output applications.



DIM	mm MIN	mm MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	3.80	4.20
J	0.45	0.75
K	13.35	13.80
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
I_B	Base Current-Continuous	-0.5	A
P_C	Collector Power Dissipation @T_a=25℃	2	W
	Collector Power Dissipation @T_C=25℃	20	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA ; I_B= 0	-150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -0.5A; V_{CE}= -10V			-0.85	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -120V; I_E= 0			-10	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-10	μ A
h_{FE}	DC Current Gain	I_C= -0.5A; V_{CE}= -10V	40		140	
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A; V_{CE}= -10V		4		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V; f= 1MHz		55		pF

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